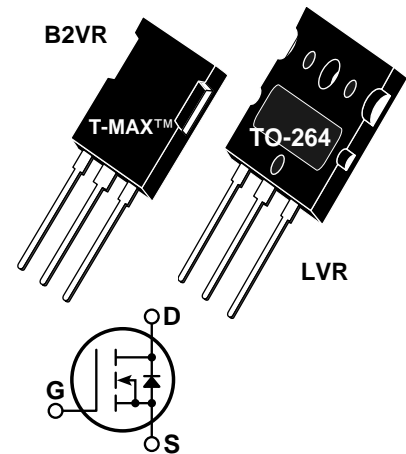


**POWER MOS V®**

Power MOS V® is a new generation of high voltage N-Channel enhancement mode power MOSFETs. This new technology minimizes the JFET effect, increases packing density and reduces the on-resistance. Power MOS V® also achieves faster switching speeds through optimized gate layout.



- **Identical Specifications: T-MAX™ or TO-264 Package**
- **Faster Switching**                      • **100% Avalanche Tested**
- **Lower Leakage**

**MAXIMUM RATINGS**

 All Ratings:  $T_C = 25^\circ\text{C}$  unless otherwise specified.

Symbol	Parameter	APT10M09	UNIT
$V_{DSS}$	Drain-Source Voltage	100	Volts
$I_D$	Continuous Drain Current @ $T_C = 25^\circ\text{C}$ ⑤	100	Amps
$I_{DM}$	Pulsed Drain Current ① ⑤	400	
$V_{GS}$	Gate-Source Voltage Continuous	$\pm 30$	Volts
$V_{GSM}$	Gate-Source Voltage Transient	$\pm 40$	
$P_D$	Total Power Dissipation @ $T_C = 25^\circ\text{C}$	625	Watts
	Linear Derating Factor	5.0	W/°C
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to 150	°C
$T_L$	Lead Temperature: 0.063" from Case for 10 Sec.	300	
$I_{AR}$	Avalanche Current ① ⑤ (Repetitive and Non-Repetitive)	100	Amps
$E_{AR}$	Repetitive Avalanche Energy ①	50	mJ
$E_{AS}$	Single Pulse Avalanche Energy ④	3000	

**STATIC ELECTRICAL CHARACTERISTICS**

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
$BV_{DSS}$	Drain-Source Breakdown Voltage ( $V_{GS} = 0V, I_D = 250\mu\text{A}$ )	100			Volts
$I_{D(on)}$	On State Drain Current ② ⑤ ( $V_{DS} > I_{D(on)} \times R_{DS(on)}$ Max, $V_{GS} = 10V$ )	100			Amps
$R_{DS(on)}$	Drain-Source On-State Resistance ② ( $V_{GS} = 10V, 0.5 I_{D[Cont.]}$ )			0.009	Ohms
$I_{DSS}$	Zero Gate Voltage Drain Current ( $V_{DS} = V_{DSS}, V_{GS} = 0V$ )			250	$\mu\text{A}$
	Zero Gate Voltage Drain Current ( $V_{DS} = 0.8 V_{DSS}, V_{GS} = 0V, T_C = 125^\circ\text{C}$ )			1000	
$I_{GSS}$	Gate-Source Leakage Current ( $V_{GS} = \pm 30V, V_{DS} = 0V$ )			$\pm 100$	nA
$V_{GS(th)}$	Gate Threshold Voltage ( $V_{DS} = V_{GS}, I_D = 2.5\text{mA}$ )	2		4	Volts

 **CAUTION:** These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

APT Website - <http://www.advancedpower.com>

**DYNAMIC CHARACTERISTICS**

**APT10M09 B2VR - LVR**

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
$C_{iss}$	Input Capacitance	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1\text{ MHz}$		10030		pF
$C_{oss}$	Output Capacitance			3730		
$C_{rss}$	Reverse Transfer Capacitance			1370		
$Q_g$	Total Gate Charge <sup>③</sup>	$V_{GS} = 10V$ $V_{DD} = 0.5 V_{DSS}$ $I_D = 0.5 I_{D[Cont.]} @ 25^\circ C$		340		nC
$Q_{gs}$	Gate-Source Charge			109		
$Q_{gd}$	Gate-Drain ("Miller") Charge			131		
$t_{d(on)}$	Turn-on Delay Time	$V_{GS} = 15V$ $V_{DD} = 0.5 V_{DSS}$ $I_D = I_{D[Cont.]} @ 25^\circ C$ $R_G = 0.6\Omega$		18		ns
$t_r$	Rise Time			36		
$t_{d(off)}$	Turn-off Delay Time			51		
$t_f$	Fall Time			9		

**SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS**

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
$I_S$	Continuous Source Current <sup>⑤</sup> (Body Diode)			100	Amps
$I_{SM}$	Pulsed Source Current <sup>① ⑤</sup> (Body Diode)			400	
$V_{SD}$	Diode Forward Voltage <sup>②</sup> ( $V_{GS} = 0V, I_S = -I_{D[Cont.]}$ )			1.3	Volts
$t_{rr}$	Reverse Recovery Time ( $I_S = -I_{D[Cont.]}, di_S/dt = 100A/\mu s$ )		270		ns
$Q_{rr}$	Reverse Recovery Charge ( $I_S = -I_{D[Cont.]}, di_S/dt = 100A/\mu s$ )		2.9		$\mu C$

**THERMAL CHARACTERISTICS**

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case			0.20	$^\circ C/W$
$R_{\theta JA}$	Junction to Ambient			40	

- ① Repetitive Rating: Pulse width limited by maximum  $T_j$
- ② Pulse Test: Pulse width < 380  $\mu s$ , Duty Cycle < 2%
- ③ See MIL-STD-750 Method 3471
- ④ Starting  $T_j = +25^\circ C$ ,  $L = 600\mu H$ ,  $R_G = 25\Omega$ , Peak  $I_L = 100A$
- ⑤ The maximum current is limited by lead temperature.

APT Reserves the right to change, without notice, the specifications and information contained herein.

